

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated device includes a first insulating film 407 formed on any one of a conductive layer 406 and an interlayer insulating film 405, a first layer pad 408 which is in a two-layer pad and which is formed on the first insulating film 407, a third insulating film 413 deposited on both of the first insulating film 407 and the first layer pad 408 of the two-layer pad, a conductive plug 411 which is arranged to connect upper and lower pads of the two-layer pad and which is formed in the third insulating film 413, a second layer pad 401 which is in the two-layer pad and which is formed on the third insulating film 413, a second insulating film 409 which is formed on any one of the conductive layer 406 and the interlayer insulating film 405 and which has a film thickness greater than that of the first insulating film 407, and a single-layer pad 421 formed on the second insulating film 409. The single-layer pad is used at the time of a wafer test, and the second layer pad of the two-layer pad is used at the time of wire bonding.